



PHPT61003NY

100 V, 3 A NPN high power bipolar transistor

3 February 2014

Product data sheet

1. General description

NPN high power bipolar transistor in a SOT669 (LFAK56) Surface-Mounted Device (SMD) power plastic package.

PNP complement: PHPT61003PY

2. Features and benefits

- High thermal power dissipation capability
- Suitable for high temperature applications up to 175 °C
- Reduced Printed-Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

3. Applications

- Power management
- Loadswitch
- Linear mode voltage regulator
- Backlighting applications

4. Quick reference data

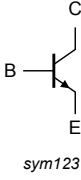
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	100	V
I_C	collector current		-	-	3	A
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms	-	-	8	A
R_{CEsat}	collector-emitter saturation resistance	$I_C = 3$ A; $I_B = 300$ mA; $t_p \leq 300$ μ s; $\delta \leq 0.02$; pulsed	-	75	110	m Ω



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter	 LFPAK56; Power-SO8 (SOT669)	
2	E	emitter		
3	E	emitter		
4	B	base		
mb	C	collector		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PHPT61003NY	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669

7. Marking

Table 4. Marking codes

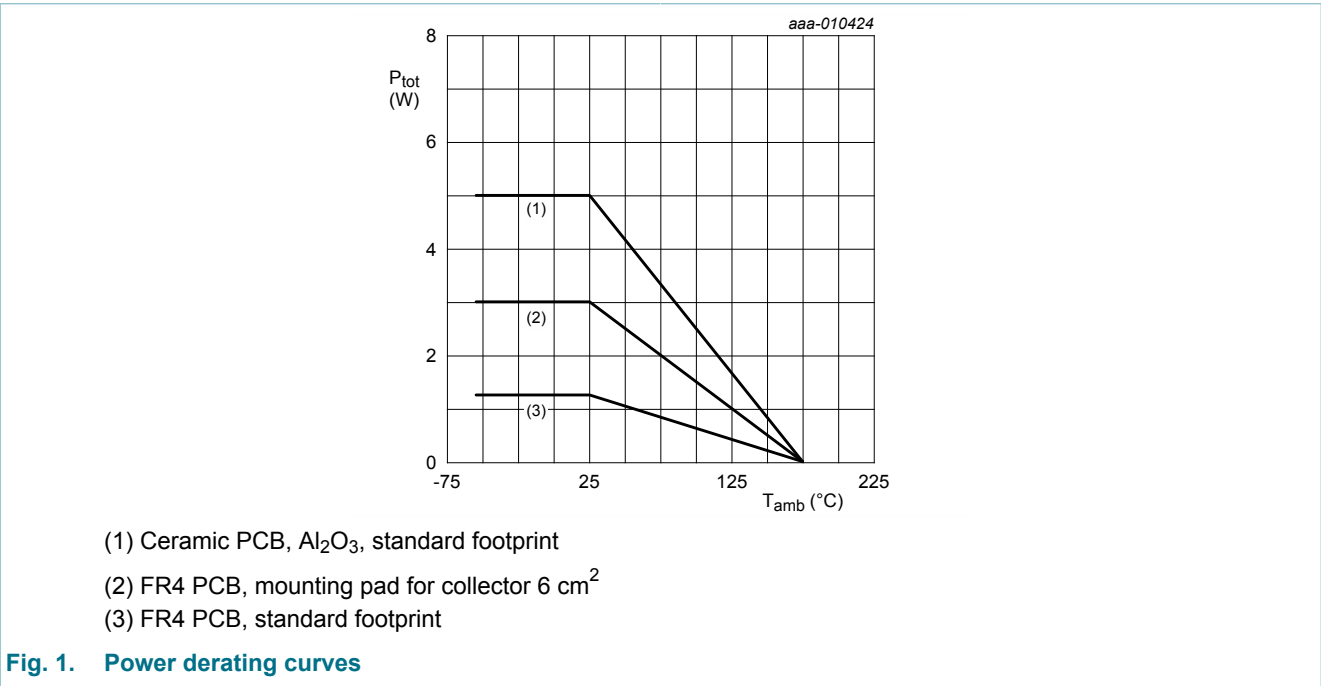
Type number	Marking code
PHPT61003NY	1003NAB

8. Limiting values

Table 5. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	100	V
V _{CEO}	collector-emitter voltage	open base		-	100	V
V _{EBO}	emitter-base voltage	open collector		-	7	V
I _C	collector current			-	3	A
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	8	A
I _B	base current			-	0.5	A
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	1.25	W
			[2]	-	3	W
			[3]	-	5	W
			[4]	-	25	W
T _j	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB) single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm².
- [3] Device mounted on an ceramic PCB; Al₂O₃; standard footprint.
- [4] Power dissipation from junction to mounting base.

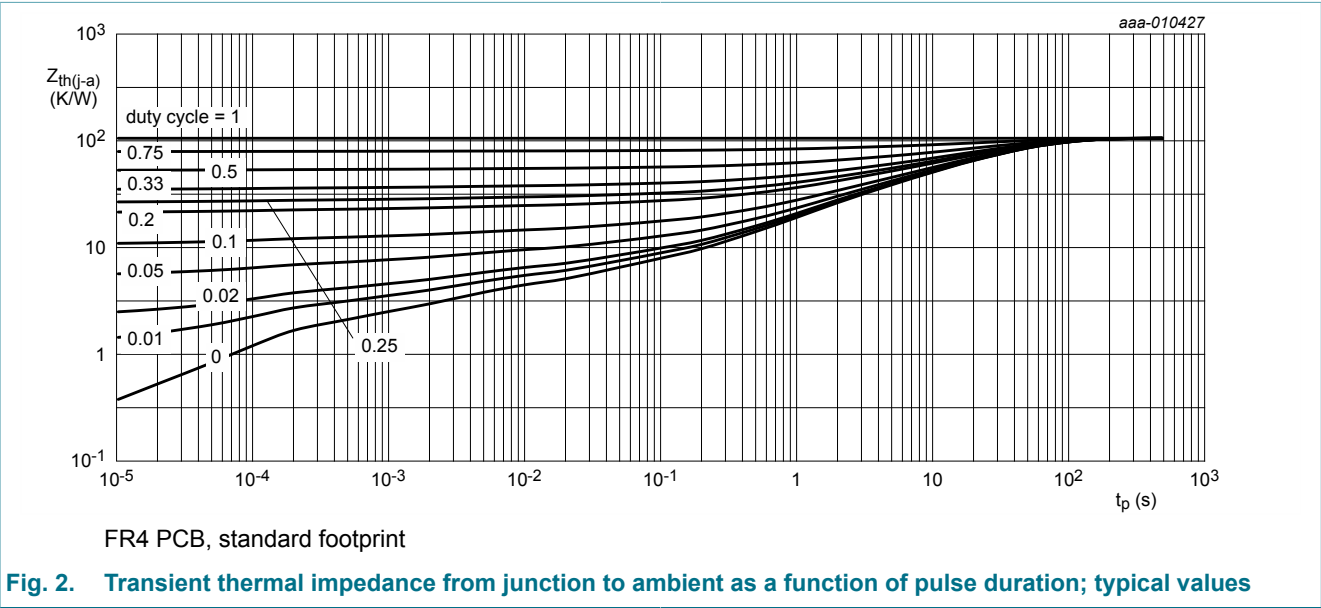


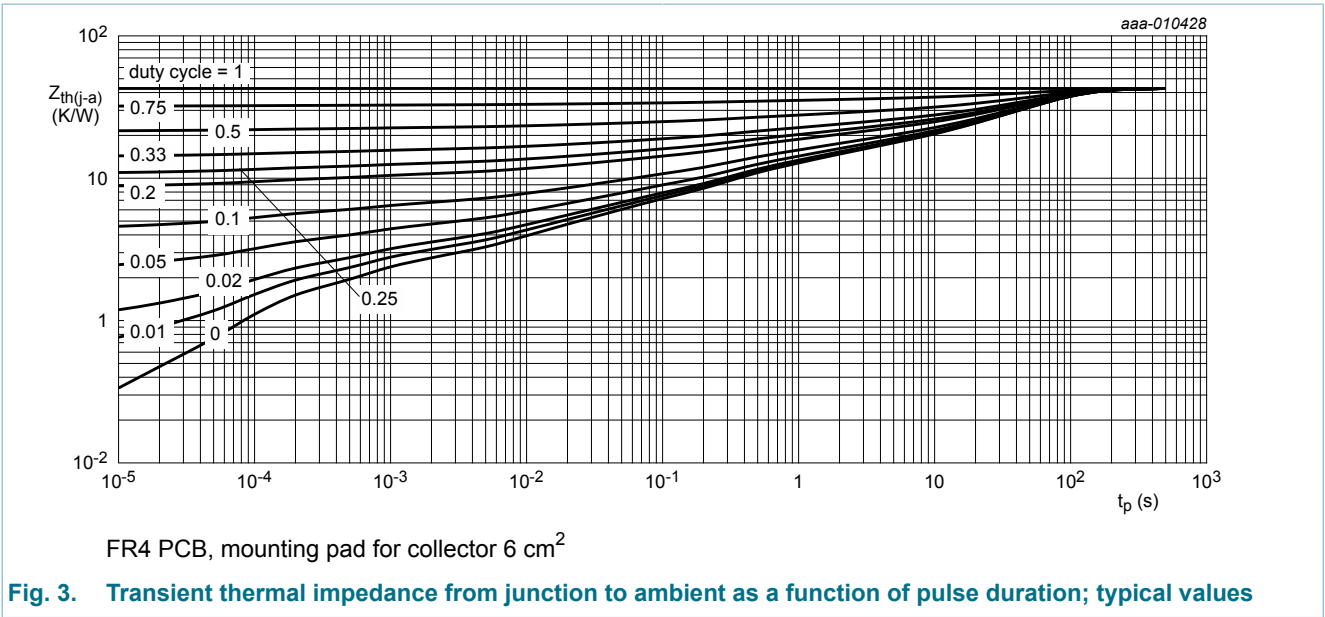
9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	115	K/W
			[2]	-	-	50	K/W
			[3]	-	-	30	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	6	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB); single-sided copper; tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB; single-sided copper; tin-plated and mounting pad for collector 6 cm².
- [3] Device mounted on an ceramic PCB; Al₂O₃; standard footprint.



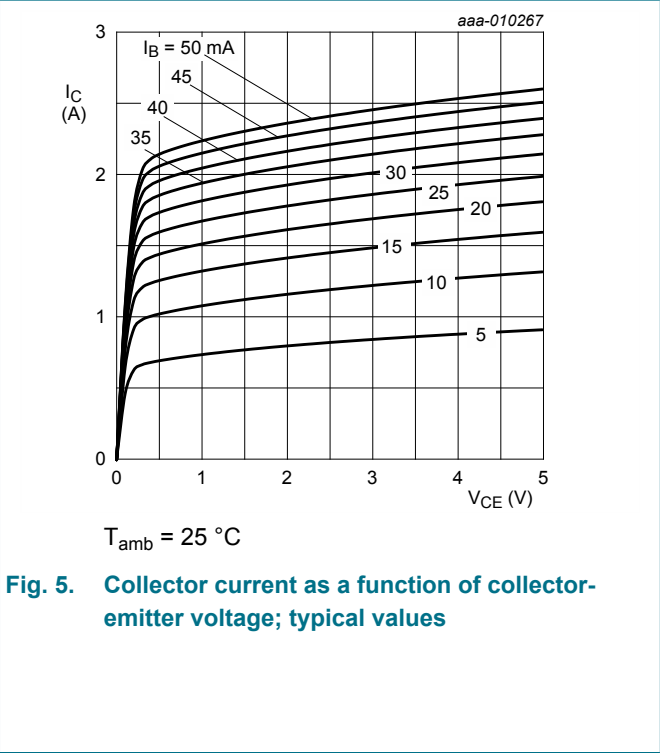
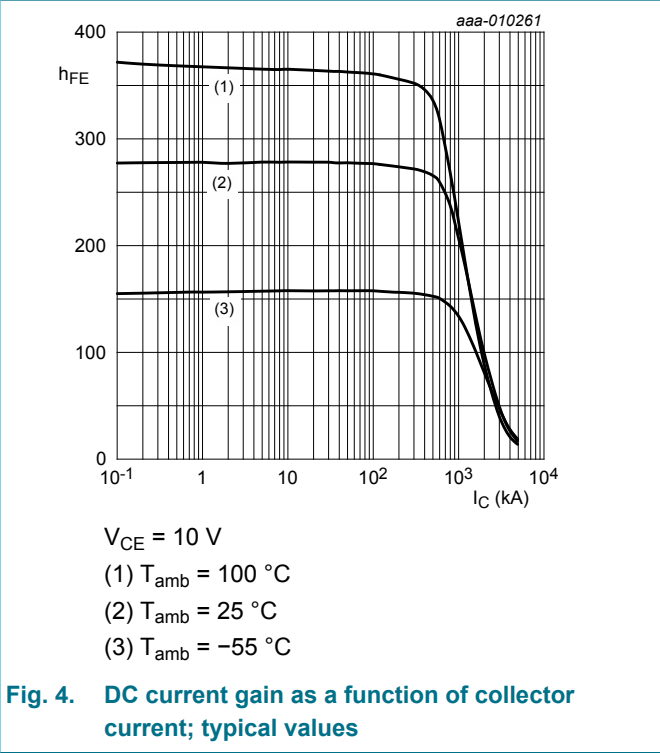


10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CBO}	collector-base cut-off current	$V_{CB} = 80\text{ V}; I_E = 0\text{ A}; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	-	100	nA
		$V_{CB} = 80\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ }^{\circ}\text{C}$	-	-	50	μA
I_{CES}	collector-emitter cut-off current	$V_{CE} = 80\text{ V}; V_{BE} = 0\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	-	100	nA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 7\text{ V}; I_C = 0\text{ A}; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	-	100	nA
h_{FE}	DC current gain	$V_{CE} = 10\text{ V}; I_C = 500\text{ mA}; t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^{\circ}\text{C}; \text{pulsed}$	150	250	-	
		$V_{CE} = 10\text{ V}; I_C = 1\text{ A}; t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^{\circ}\text{C}; \text{pulsed}$	80	250	-	
		$V_{CE} = 10\text{ V}; I_C = 2\text{ A}; t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^{\circ}\text{C}; \text{pulsed}$	20	100	-	
		$V_{CE} = 10\text{ V}; I_C = 3\text{ A}; t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^{\circ}\text{C}; \text{pulsed}$	10	40	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 1\text{ A}; I_B = 50\text{ mA}; \text{pulsed}; t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	90	150	mV
		$I_C = 3\text{ A}; I_B = 300\text{ mA}; \text{pulsed}; t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	225	330	mV
R_{CEsat}	collector-emitter saturation resistance	$I_C = 1\text{ A}; I_B = 50\text{ mA}; \text{pulsed}; t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	90	150	m Ω
		$I_C = 3\text{ A}; I_B = 300\text{ mA}; t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; \text{pulsed}$	-	75	110	m Ω
V_{BEsat}	base-emitter saturation voltage	$I_C = 1\text{ A}; I_B = 50\text{ mA}; \text{pulsed}; t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	0.86	1	V
		$I_C = 2\text{ A}; I_B = 200\text{ mA}; \text{pulsed}; t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	1	1.2	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = 2\text{ V}; I_C = 0.1\text{ A}; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	0.67	0.85	V
t_d	delay time	$V_{CC} = 12.5\text{ V}; I_C = 1\text{ A}; I_{Bon} = 0.05\text{ A}; I_{Boff} = -0.05\text{ A}; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	20	-	ns
t_r	rise time		-	300	-	ns
t_{on}	turn-on time		-	320	-	ns
t_s	storage time		-	830	-	ns
t_f	fall time		-	470	-	ns
t_{off}	turn-off time		-	1300	-	ns

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_T	transition frequency	$V_{CE} = 10\text{ V}; I_C = 100\text{ mA}; f = 100\text{ MHz}; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	140	-	MHz
C_c	collector capacitance	$V_{CB} = 10\text{ V}; I_E = 0\text{ A}; i_e = 0\text{ A}; f = 1\text{ MHz}; T_{amb} = 25\text{ }^{\circ}\text{C}$	-	11	-	pF



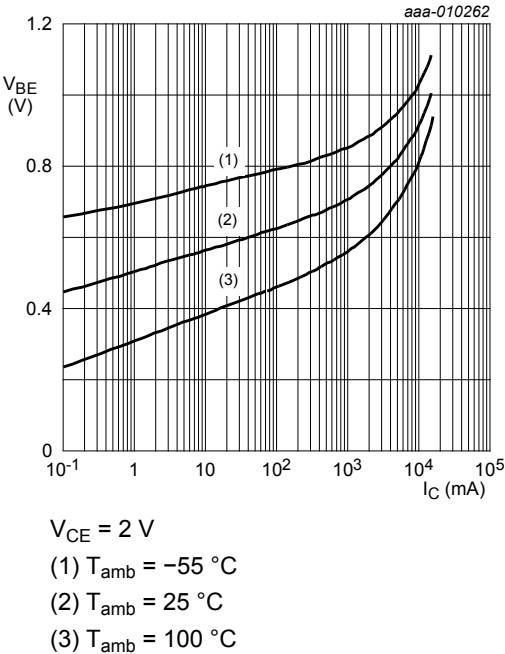


Fig. 6. Base-emitter voltage as a function of collector current; typical values

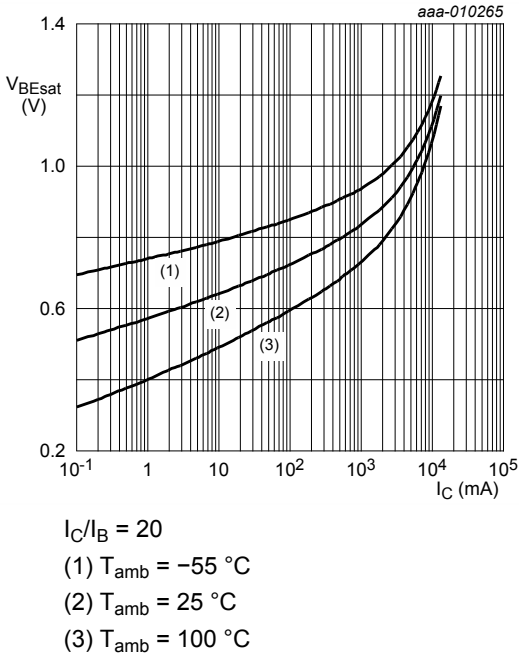


Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

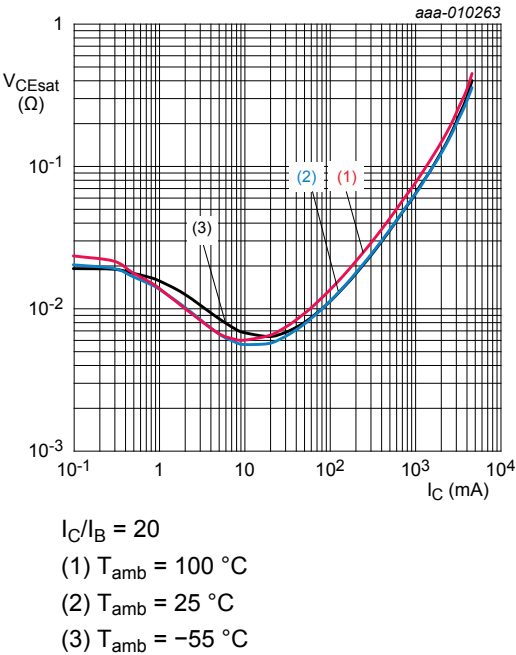


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

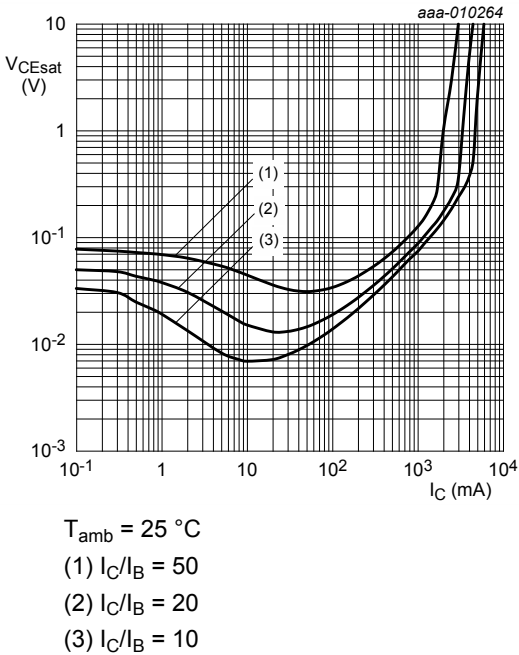
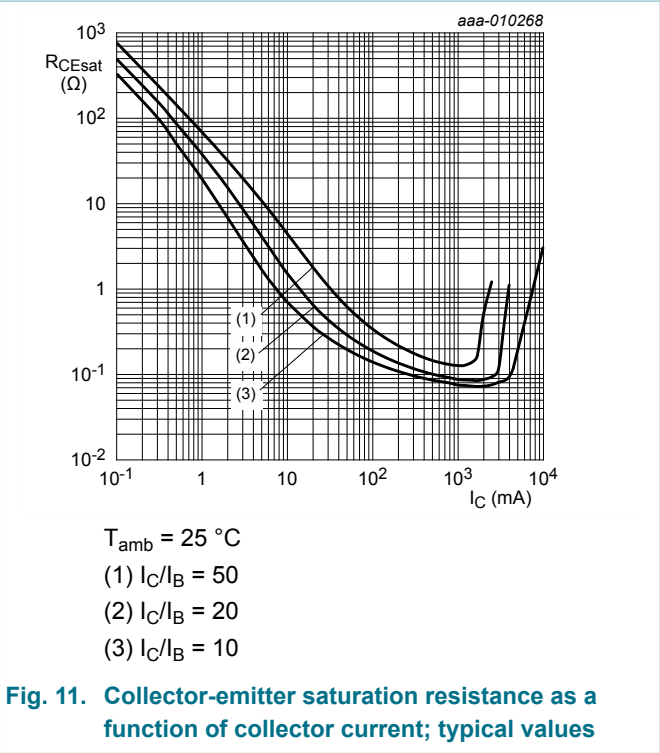
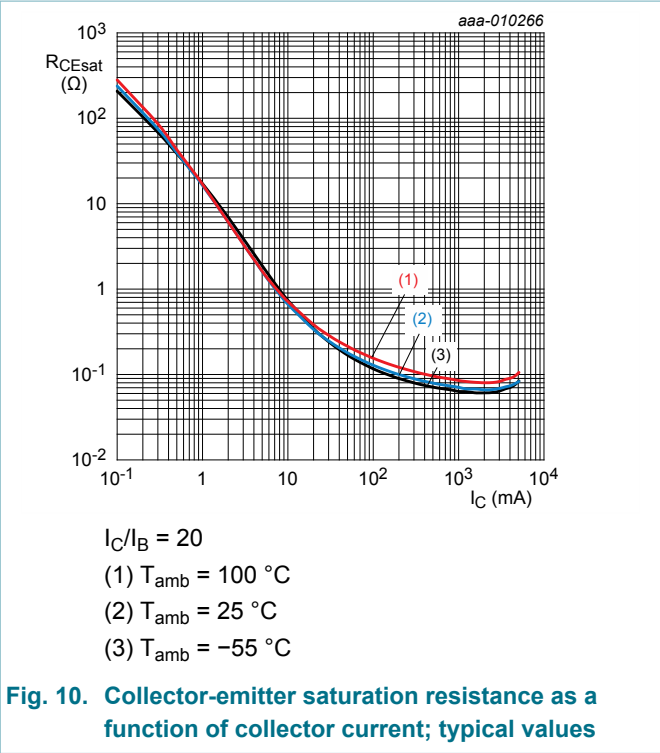


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values



11. Test information

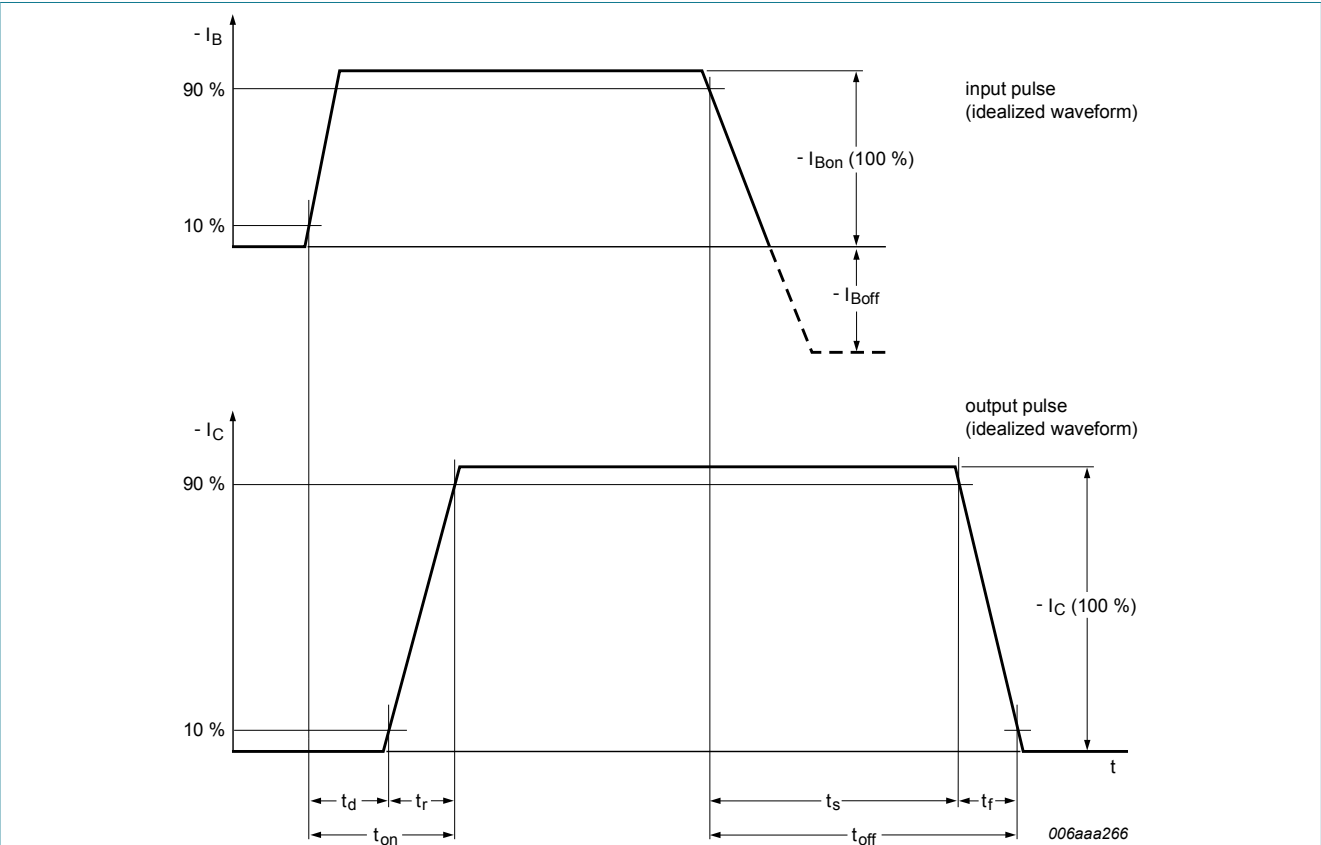


Fig. 12. BISS transistor switching time definition

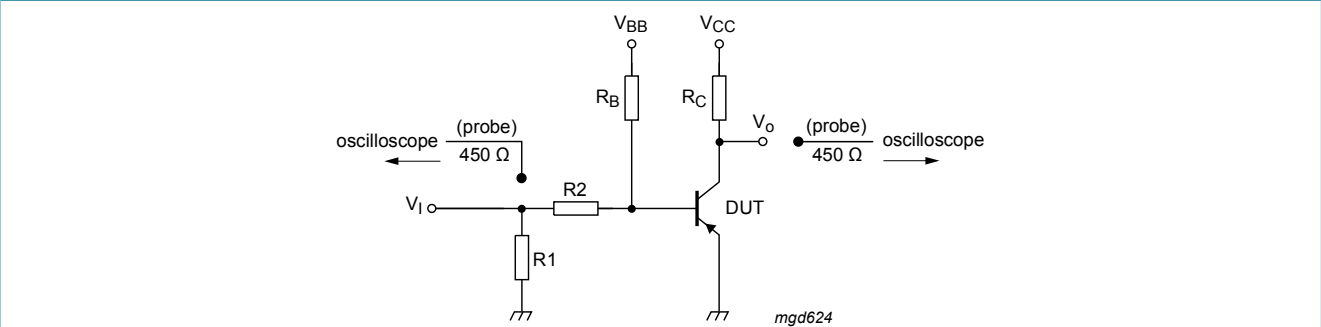


Fig. 13. Test circuit for switching times

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline

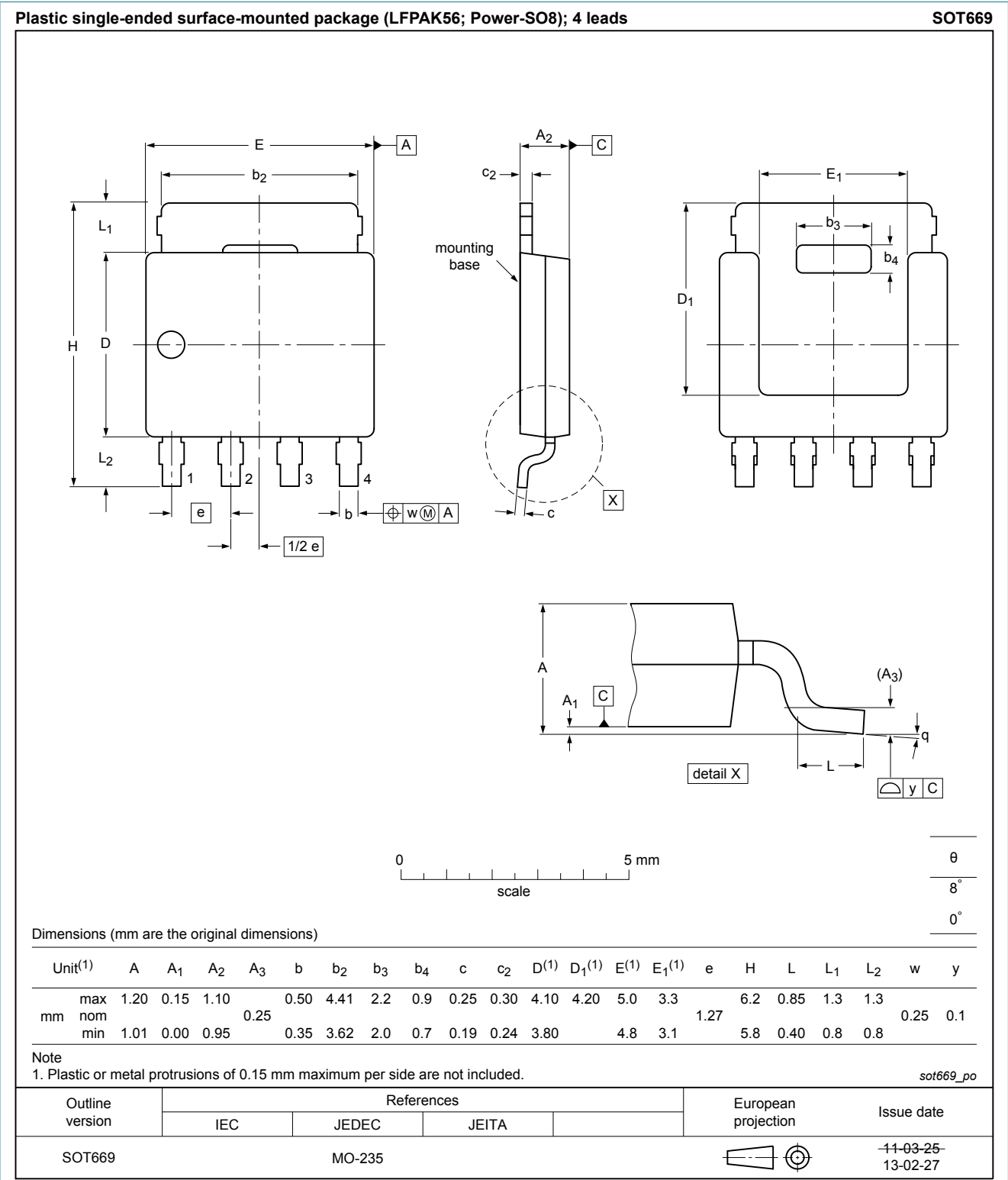


Fig. 14. Package outline LPAK56; Power-SO8 (SOT669)

13. Soldering

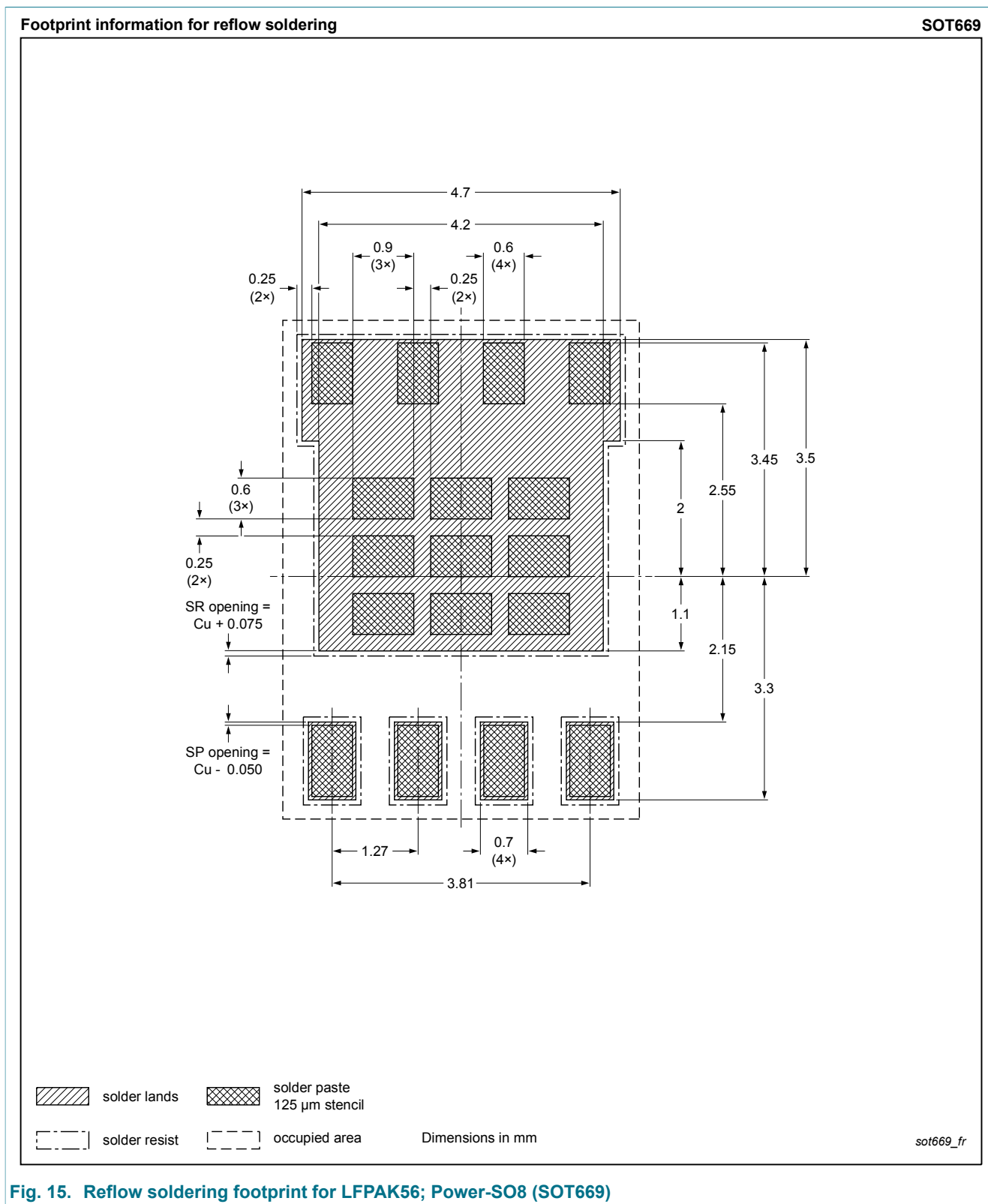


Fig. 15. Reflow soldering footprint for LPAK56; Power-SO8 (SOT669)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PHPT61003NY v.3	20140203	Product data sheet	-	PHPT61003NY v.2
Modifications:	PNP corrected to NPN			
PHPT61003NY v.2	20131213	Product data sheet	-	PHPT61003NY v.1
Modifications:	editorial update			
PHPT61003NY v.1	20140113	Product data sheet	-	

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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